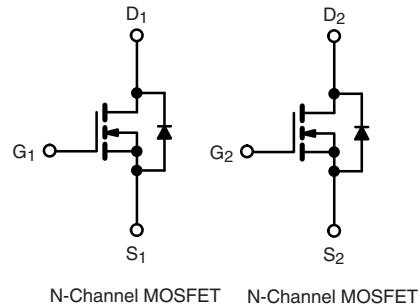


Dual N-Channel 60 V (D-S) MOSFET

Features

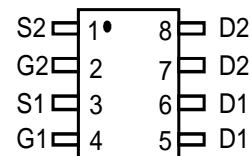
- TrenchFET<sup>®</sup> power MOSFET
- 100 % R<sub>g</sub> and UIS tested



Product Summary

V <sub>DS</sub>	60V
I <sub>D</sub> (at V <sub>GS</sub> =10V)	7A
R <sub>DS(ON)</sub> (at V <sub>GS</sub> =10V)	< 19mΩ
R <sub>DS(ON)</sub> (at V <sub>GS</sub> =4.5V)	< 23mΩ

Top View



ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current	I <sub>D</sub>	T <sub>C</sub> = 25 °C	7
		T <sub>C</sub> = 125 °C	4
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	3.6	A
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	28	
Single Pulse Avalanche Current	I <sub>AS</sub>	18	
Single Pulse Avalanche Energy	E <sub>AS</sub>	16.2	mJ
Maximum Power Dissipation <sup>b</sup>	P <sub>D</sub>	T <sub>C</sub> = 25 °C	4
		T <sub>C</sub> = 125 °C	1.3
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATING S			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R <sub>thJA</sub>	110	°C/W
Junction-to-Foot (Drain)	R <sub>thJF</sub>	34	

Notes

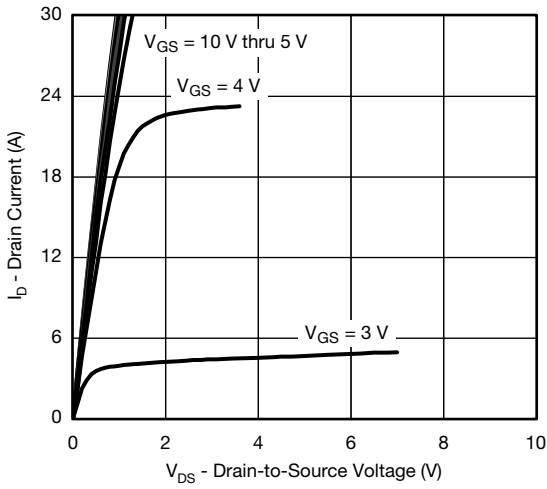
- Package limited.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).

SPECIFICATIONS (T <sub>C</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		60	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		1.5	2.0	2.5	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V	-	-	1	μA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> ≥ 5 V	20	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 4.5 A-		19	21	mΩ
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 4 A-		23	25	
Forward Transconductance <sup>f</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 4.5 A		-	15	-	S
<b>Dynamic <sup>b</sup></b>							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 25 V, f = 1 MHz	-	600	750	pF
Output Capacitance	C <sub>oss</sub>			-	110	140	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	50	62	
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 5.3 A	-	11.7	18	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			-	1.8	2.7	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	2.8	4.2	
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.3	-	6	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 30 V, R <sub>L</sub> = 6.8 Ω I <sub>D</sub> ≅ 4.4 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω		-	7	11	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			-	3.3	5	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	22.4	33.5	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	2.1	3.2	
<b>Source-Drain Diode Ratings and Characteristics <sup>b</sup></b>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	28	A
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 2 A, V <sub>GS</sub> = 0 V		-	0.75	1.1	V

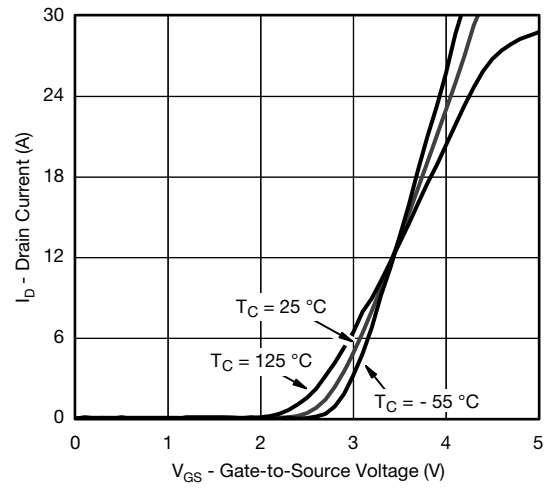
**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

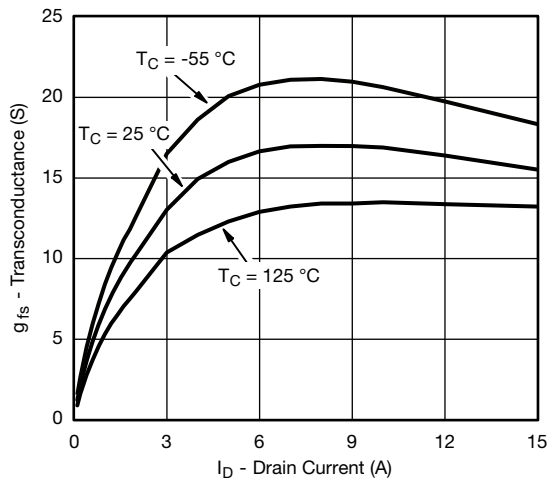
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



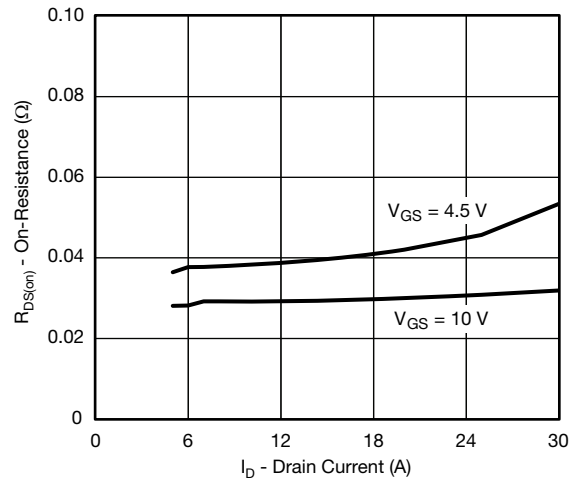
**Output Characteristics**



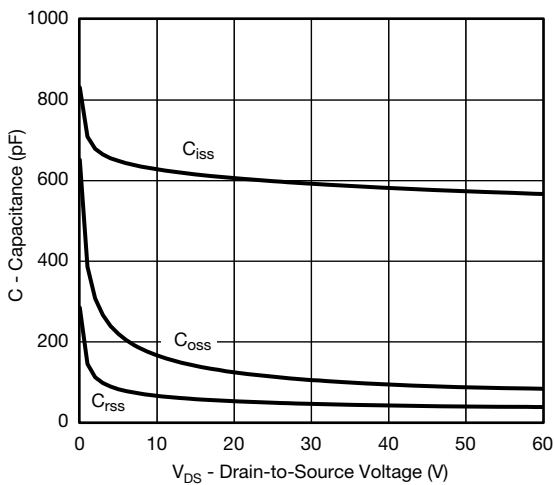
**Transfer Characteristics**



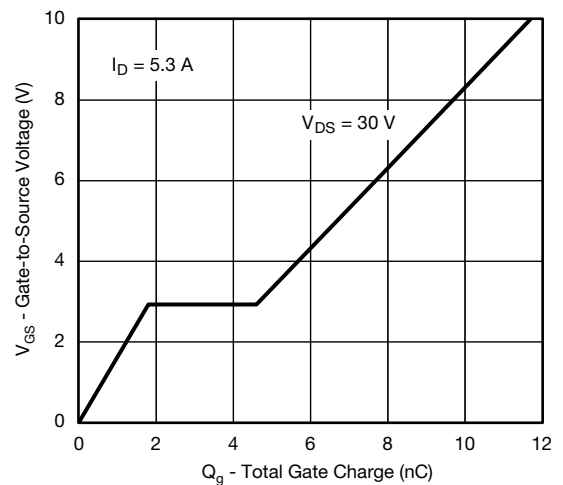
**Transconductance**



**On-Resistance vs. Drain Current**

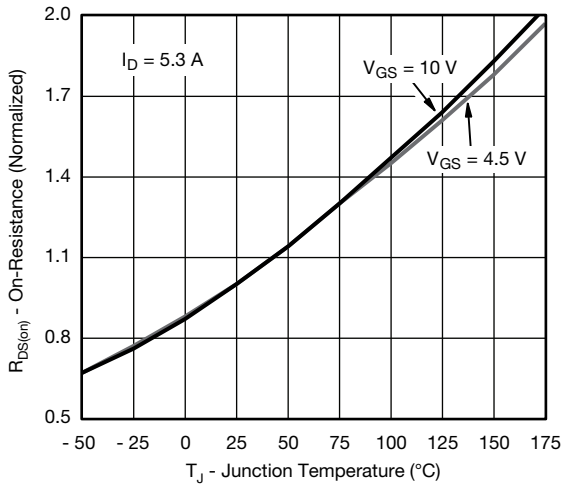


**Capacitance**

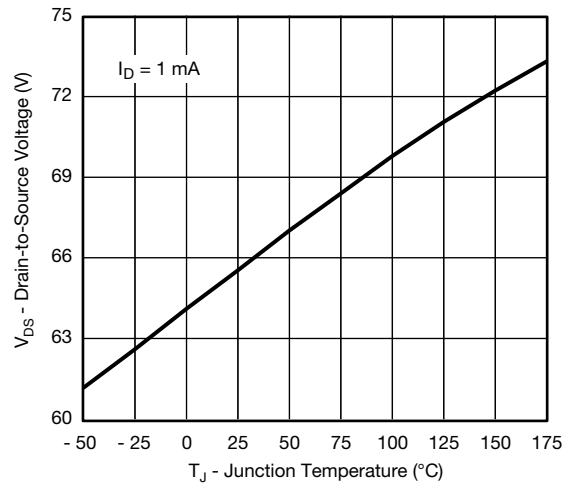


**Gate Charge**

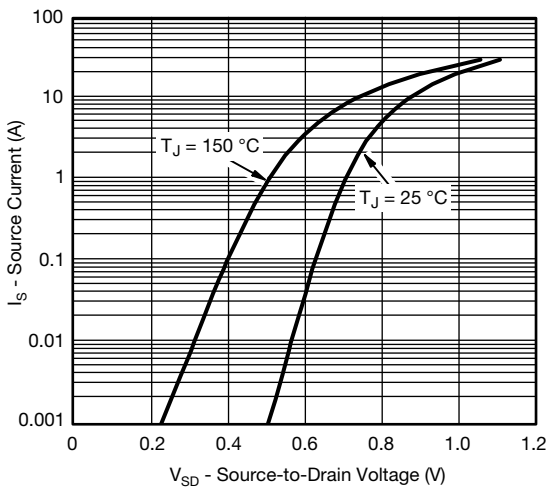
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



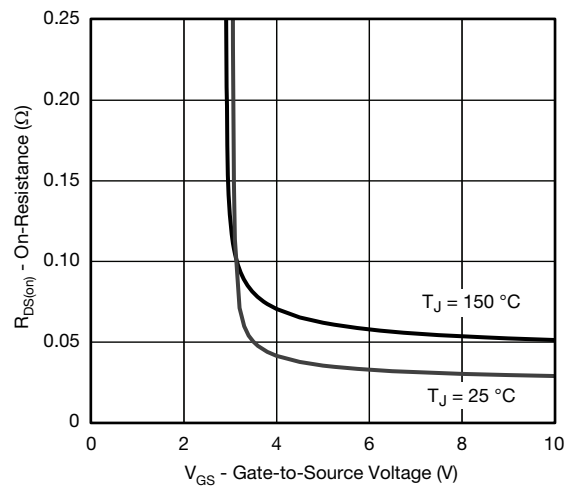
**On-Resistance vs. Junction Temperature**



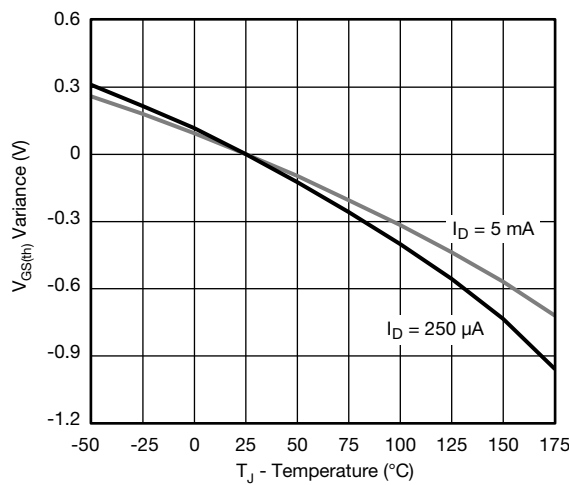
**Drain Source Breakdown vs. Junction Temperature**



**Source Drain Diode Forward Voltage**

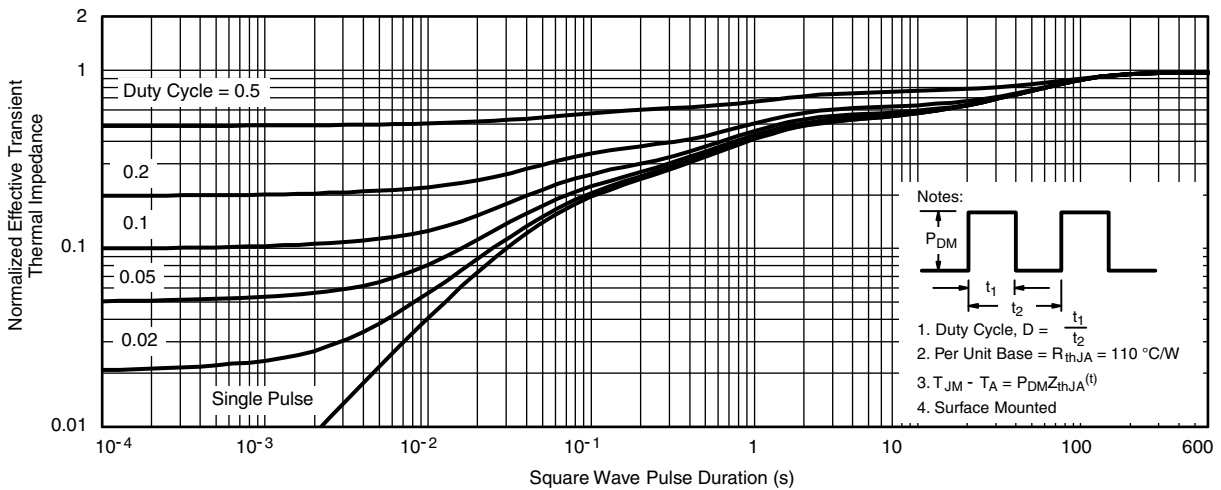
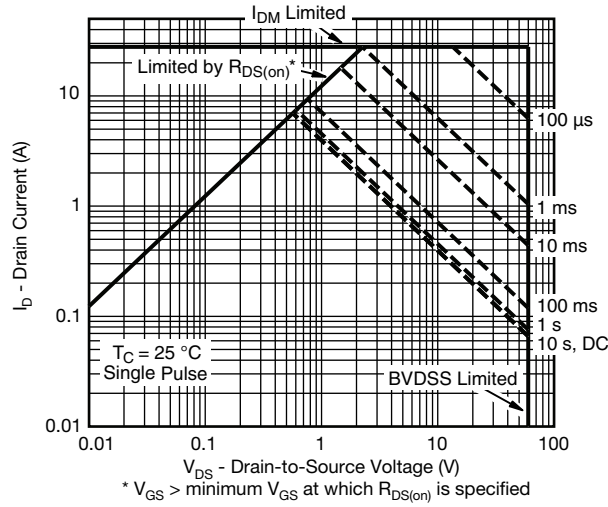


**On-Resistance vs. Gate-to-Source Voltage**



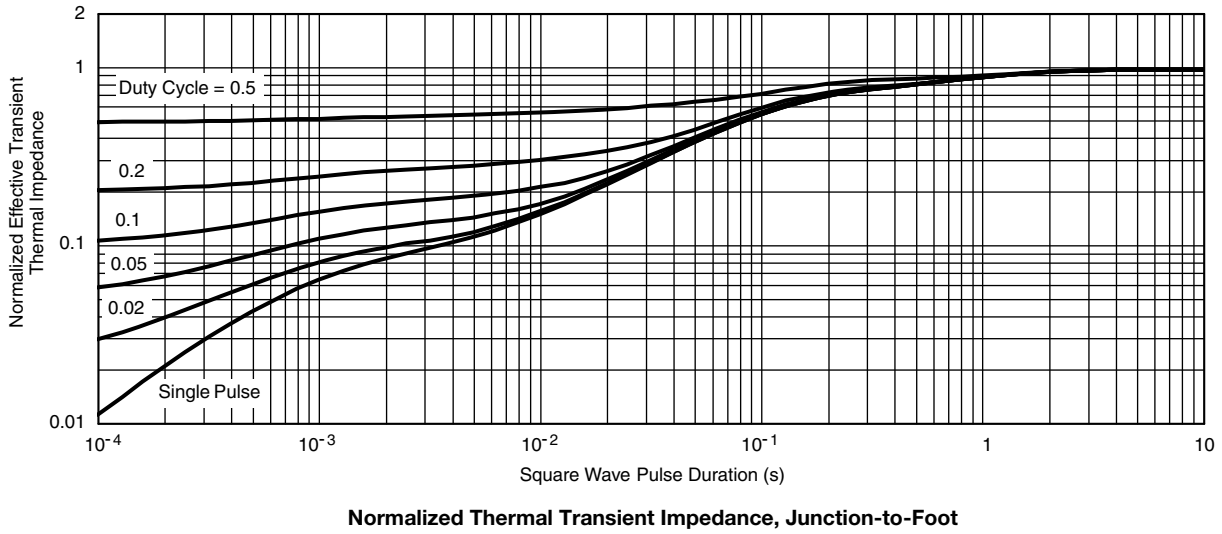
**Threshold Voltage**

**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

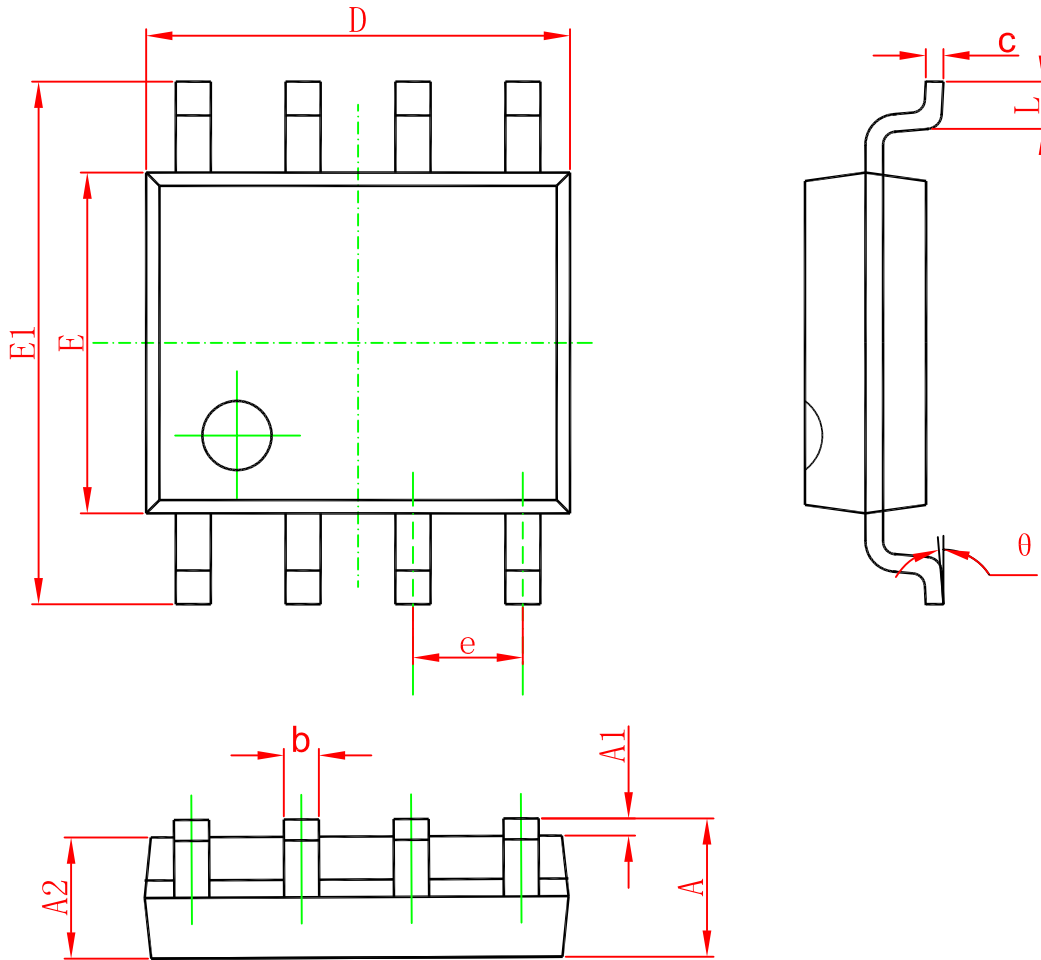


**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

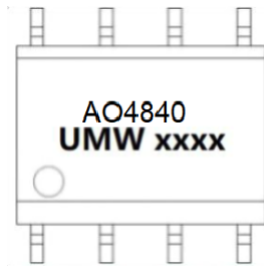


SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

**Marking**



**Ordering information**

Order code	Package	Baseqty	Deliverymode
UMW AO4840	SOP-8	3000	Tape and reel